



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23-3L Plastic-Encapsulate Transistors

2SB624 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.7 A

Collector-base voltage

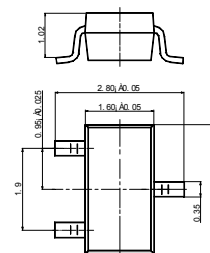
$V_{(BR)CBO}$: -30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-23-3L

1. BASE
2. EMITTER
3. COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{ mA}, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30\text{ V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{ V}, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=-1\text{ V}, I_C=-100\text{ mA}$	110		400	
	$h_{FE(2)}^*$	$V_{CE}=-1\text{ V}, I_C=-700\text{ mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=-700\text{ mA}, I_B=-70\text{ mA}$			-0.6	V
Base-emitter voltage	$V_{BE(on)}^*$	$V_{CE}=-6\text{ V}, I_C=-10\text{ mA}$	-0.6		-0.7	V
Transition frequency	f_T	$V_{CE}=-6\text{ V}, I_C=-10\text{ mA}$	140			MHz

* Pulse test : Pulse width $\leq 350\mu s$, Duty Cycle $\leq 2\%$.

CLASSIFICATION OF $h_{FE(1)}$

Marking	BV1	BV2	BV3	BV4	BV5
Range	110-180	135-220	170-270	200-320	250-400